

thermal treating the resulting semiconductor substrate for reducing a native oxide film naturally formed on the semiconductor substrate and for forming a first silicide film on the semiconductor substrate;

removing an unreacted first metal film selectively;

forming a second metal film on the semiconductor substrate; and

thermal treating the resulting semiconductor substrate for forming a second silicide film on a surface of the semiconductor substrate which includes a region where the first silicide film is formed.

2. (Amended) A method of manufacturing a semiconductor device according to claim 1, wherein the first metal film comprises titanium.

A' 3. (Amended) A method of manufacturing a semiconductor device according to claim 1, wherein the second metal film comprises cobalt.

4. (Amended) A method of manufacturing a semiconductor device according to claim 1, wherein said thermal treating for reducing the native oxide film and forming the first silicide film is carried out at a temperature of 500°C or less.

Ae 10. (Amended) A method of manufacturing a semiconductor device according to claim 1, further comprising heating the substrate when the first metal film is formed and

this heating of the substrate also serves as the thermal treating for reducing the native oxide film and forming the first silicide film.

12. (*Unamended*) A semiconductor device manufactured by a method comprising steps of:

forming a first metal film having a reducing property on a semiconductor substrate;

thermal treating the resulting semiconductor substrate for reducing a native oxide film naturally formed on the semiconductor substrate and for forming a first silicide film on the semiconductor substrate;

removing an unreacted first metal film selectively;

forming a second metal film on the semiconductor substrate; and

thermal treating the resulting semiconductor substrate for forming a second silicide film on a surface of the semiconductor substrate which includes a region where the first silicide film is formed.

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Please add the following new claims:

13. (*New*) A method of making a semiconductor device, the method comprising:

forming a first metal inclusive film having a reducing property over at least a semiconductor substrate;

after forming the first metal inclusive film, thermal treating at least the semiconductor substrate to reduce a native oxide film formed over at least the semiconductor substrate and to form a first silicide film over at least the semiconductor substrate;

forming a second metal inclusive film over at least semiconductor substrate and the first silicide film; and

after forming the second metal inclusive film, thermal treating at least the semiconductor substrate to form a second silicide film which includes a region where the first silicide film was formed.

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14. (New) The method of claim 13, wherein the first silicide film is at least partially located at a top portion of a gate electrode.

15. (New) The method of claim 13, wherein the second silicide film is at least partially located at a top portion of a gate electrode.

16. (New) The method of claim 13, further comprising removing at least part of an unreacted portion of the first metal film after forming the first silicide film but before forming the second silicide film.